Abstracts

GaAs Monolithic Transferred-Electron Devices for Millimeter Wave Applications

P.A. Rolland, A. Cappy and M.R. Friscourt. "GaAs Monolithic Transferred-Electron Devices for Millimeter Wave Applications." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 427-430.

In this paper the authors point out the existence of two different operating modes in a planar GaAs transferred-electron oscillator with a current limiting MESFET cathode. The respective advantages and drawbacks of these two modes are discussed on the basis of further monolithic integration. The influence of the operating conditions on the RF performance are given in the 100 GHz window.

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